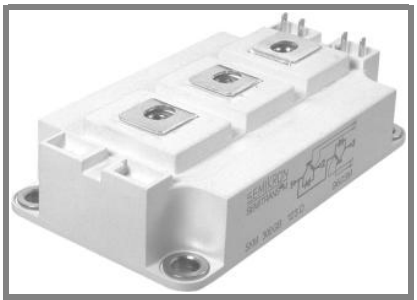
SKM 400GB123D



SEMITRANS® 3

IGBT Modules

SKM 400GB123D

Features

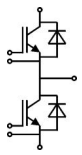
- MOS input (voltage controlled)
- N channel, homgeneous Si
- Low inductance case
- Very low tail current with low temperature dependence
- High short circuit capability, self limiting to 6 x I_{cnom}
- Latch-up free
- Fast & soft CAL diodes
- Isolated copper baseplate using DBC Direct Copper Bonding Technology
- Large clearance (12 mm) and creepage distances (20 mm)

Typical Applications

- AC inverter drives
- UPS

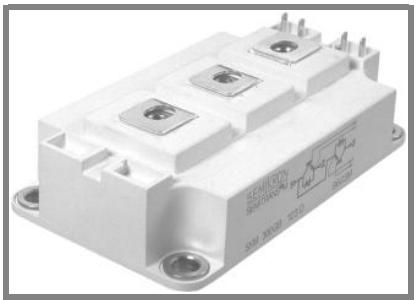
Absolute Maximum Ratings			T_c = 25 °C, unless otherwise specified	
Symbol	**Conditions**		**Values**	**Units**
IGBT				
V_{CES}	T_j = 25 °C		1200	V
I_C	T_j = 150 °C	T_{case} = 25 °C	400	A
		T_{case} = 80 °C	330	A
I_{CRM}	I_{CRM}=2xI_{Cnom}		600	A
V_{GES}			± 20	V
t_{psc}	V_{CC} = 600 V; $V_{GE} \leq$ 20 V; V_{CES} < 1200 V	T_j = 125 °C	10	µs
Inverse Diode				
I_F	T_j = 150 °C	T_{case} = 25 °C	390	A
		T_{case} = 80 °C	260	A
I_{FRM}	I_{FRM}=2xI_{Fnom}		600	A
I_{FSM}	t_p = 10 ms; sin.	T_j = 150 °C	2880	A
Module				
$I_{t(RMS)}$			500	A
T_{vj}			- 40...+ 150	°C
T_{stg}			- 40...+ 125	°C
V_{isol}	AC, 1 min.		2500	V

Characteristics			T_c = 25 °C, unless otherwise specified			
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
IGBT						
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 12 mA		4,5	5,5	6,5	V
I_{CES}	V_{GE} = 0 V, V_{CE} = V_{CES}	T_j = 25 °C		0,1	0,3	mA
V_{CE0}		T_j = 25 °C		1,4	1,6	V
		T_j = 125 °C		1,6	1,8	V
r_{CE}	V_{GE} = 15 V	T_j = 25°C		3,66	4,66	mΩ
		T_j = 125°C		5	6,33	mΩ
$V_{CE(sat)}$	I_{Cnom} = 300 A, V_{GE} = 15 V	T_j = °$C_{chiplev.}$		2,5	3	V
C_{ies}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz		22	30	nF
C_{oes}				3,3	4	nF
C_{res}				1,2	1,6	nF
Q_G	V_{GE} = -8V - +20V			3000		nC
R_{Gint}	T_j = °C			1,25		Ω
$t_{d(on)}$	R_{Gon} = 3,3 Ω	V_{CC} = 600V		200	400	ns
t_r		I_C= 300A		115	220	ns
E_{on}		T_j = 125 °C		38		mJ
$t_{d(off)}$	R_{Goff} = 3,3 Ω	V_{GE} = ± 15V		720	900	ns
t_f				80	100	ns
E_{off}				40		mJ
$R_{th(j-c)}$	per IGBT				0,05	K/W



GB

SKM 400GB123D



SEMITRANS® 3

IGBT Modules

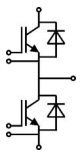
SKM 400GB123D

Features

- MOS input (voltage controlled)
- N channel, homgeneous Si
- Low inductance case
- Very low tail current with low temperature dependence
- High short circuit capability, self limiting to 6 x I_{cnom}
- Latch-up free
- Fast & soft CAL diodes
- Isolated copper baseplate using DBC Direct Copper Bonding Technology
- Large clearance (12 mm) and creepage distances (20 mm)

Typical Applications

- AC inverter drives
- UPS



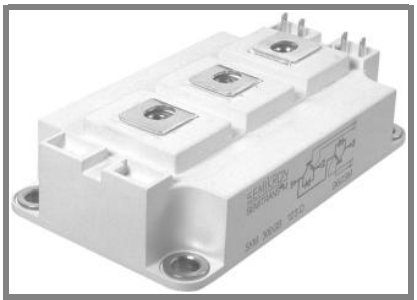
GB

Characteristics

Symbol	Conditions		min.	typ.	max.	Units
Inverse Diode						
$V_F = V_{EC}$	I_{Fnom} = 300 A; V_{GE} = 0 V	T_j = 25 °C$_{chiplev.}$		2	2,5	V
		T_j = 125 °C$_{chiplev.}$		1,8		V
V_{F0}		T_j = 25 °C		1,1	1,2	V
		T_j = 125 °C				V
r_F		T_j = 25 °C		3	4,3	mΩ
		T_j = 125 °C				mΩ
I_{RRM}	I_F = 300 A	T_j = 125 °C		140		A
Q_{rr}	di/dt = 2000 A/µs			13		µC
E_{rr}	V_{GE} = 0 V; V_{CC} = 600 V					mJ
$R_{th(j-c)D}$	per diode				0,125	K/W
Module						
L_{CE}				15	20	nH
$R_{CC'+EE'}$	res., terminal-chip	T_{case}= 25 °C		0,35		mΩ
		T_{case}= 125 °C		0,5		mΩ
$R_{th(c-s)}$	per module				0,038	K/W
M_s	to heat sink M6		3		5	Nm
w					325	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.



SEMITRANS® 3

IGBT Modules

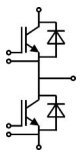
SKM 400GB123D

Features

- MOS input (voltage controlled)
- N channel, homgeneous Si
- Low inductance case
- Very low tail current with low temperature dependence
- High short circuit capability, self limiting to 6 x I_{cnom}
- Latch-up free
- Fast & soft CAL diodes
- Isolated copper baseplate using DBC Direct Copper Bonding Technology
- Large clearance (12 mm) and creepage distances (20 mm)

Typical Applications

- AC inverter drives
- UPS

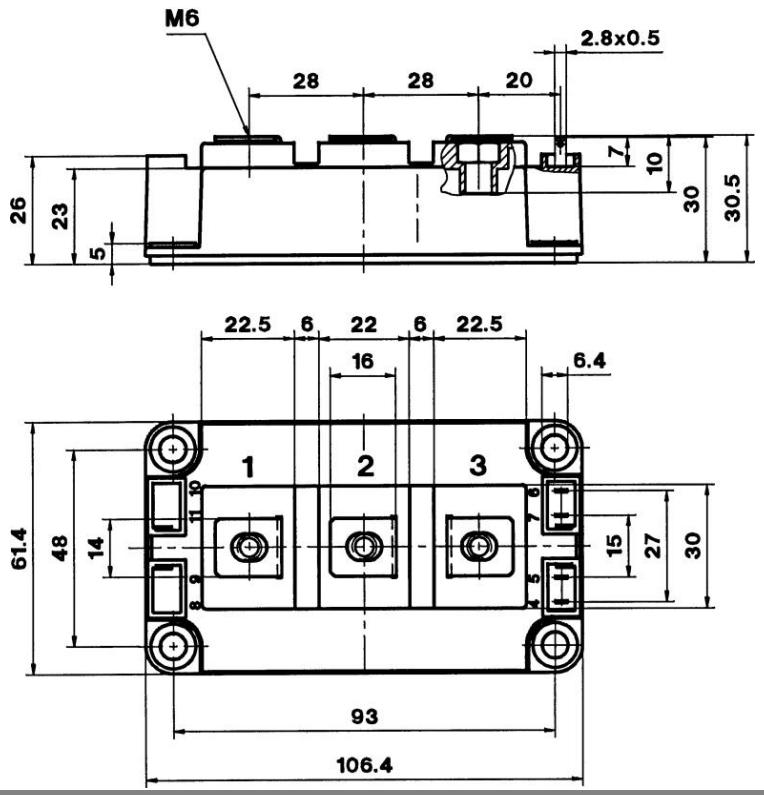


GB

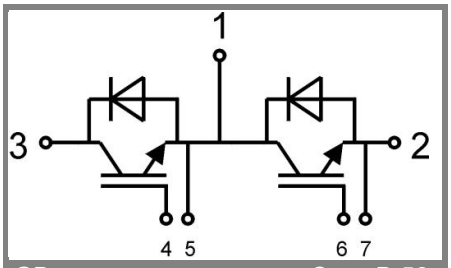
Z_{th} Symbol	Conditions	Values	Units
$Z_{th(j-c)I}$			
R_i	i = 1	32	mk/W
R_i	i = 2	14	mk/W
R_i	i = 3	3,4	mk/W
R_i	i = 4	0,6	mk/W
tau_i	i = 1	0,0447	s
tau_i	i = 2	0,0122	s
tau_i	i = 3	0,004	s
tau_i	i = 4	0,0002	s
$Z_{th(j-c)D}$			
R_i	i = 1	80	mk/W
R_i	i = 2	33	mk/W
R_i	i = 3	10,2	mk/W
R_i	i = 4	1,8	mk/W
tau_i	i = 1	0,05	s
tau_i	i = 2	0,0057	s
tau_i	i = 3	0,0034	s
tau_i	i = 4	0,0003	s

UL Recognized File 63 532

CASED56



Case D 56



GB Case D 56

